

Page 1 of 13  <b>FORM PTO-1449</b>  LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	Atty. Docket No.: H0004606 (1139.1135101)	Serial No.: 10/607,629
	Applicant: Jae-Hyun Ryou et al.	
	Filing Date: June 27, 2003	Group Art: <del>unknown</del> 2828

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## FORM PTO-1449

Page 2 of 13

Atty. Docket No.:

H0004606

(1139.1135101)

Serial No.:

10/607,629

LIST OF PATENTS AND PUBLICATIONS FOR  
APPLICANT'S INFORMATION  
DISCLOSURE STATEMENT

Applicant: Jae-Hyun Ryou et al.

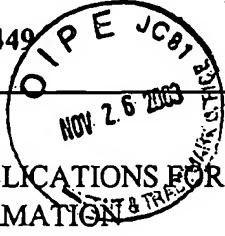
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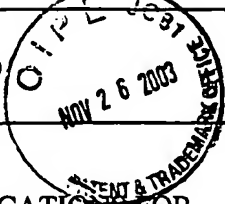
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Page 3 of 13	<b>FORM PTO-1449</b> 	Atty. Docket No.: H0004606 (1139.1135101)	Serial No.: 10/607,629
		Applicant: Jae-Hyun Ryou et al.	
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>		Filing Date: June 27, 2003	Group Art: <del>unknown</del> 2828

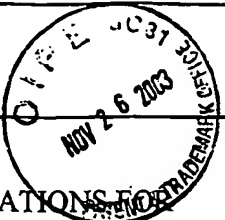
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Page 4 of 13	<b>FORM PTO-1449</b> 	Atty. Docket No.: H0004606 (1139.1135101)	Serial No.: 10/607,629
		Applicant: Jae-Hyun Ryou et al.	
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Page 5 of 13	<b>FORM PTO-1449</b> 	Atty. Docket No.: H0004606 (1139.1135101)	Serial No.: 10/607,629
		Applicant: Jae-Hyun Ryou et al.	
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>		Filing Date: June 27, 2003	Group Art: <u>unknown 2828</u>

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Page 6 of 13	<b>FORM PTO-1449</b> 	Atty. Docket No.: H0004606 (1139.1135101)	Serial No.: 10/607,629
		Applicant: Jae-Hyun Ryou et al.	
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		Filing Date: June 27, 2003	Group Art: <del>unknown</del> 2828

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Page 7 of 13	<b>FORM PTO-1449</b> 	Atty. Docket No.: H0004606 (1139.1135101)	Serial No.: 10/607,629
		Applicant: Jae-Hyun Ryou et al.	
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>		Filing Date: June 27, 2003	Group Art: <del>unknown</del> 2828

Examiner Initial	Document No.	Date	Name	Class	Sub Class	Filing Date If Appropriate
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Page 8 of 13  <b>FORM PTO-1449</b>	Atty. Docket No.: H0004606 (1139.1135101)	Serial No.: 10/607,629
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	Applicant: Jae-Hyun Ryou et al.	
	Filing Date: June 27, 2003	Group Art: <del>unknown</del> 2828



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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	Applicant: Jae-Hyun Ryou et al.	
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Page 10 of 13  <b>FORM PTO-1449</b>	Atty. Docket No.: H0004606 (1139.1135101)	Serial No.: 10/607,629
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	Applicant: Jae-Hyun Ryou et al.	
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Atty. Docket No.:  
H0004606  
(1139.1135101)

Serial No.:  
10/607,629

LIST OF PATENTS AND PUBLICATIONS FOR  
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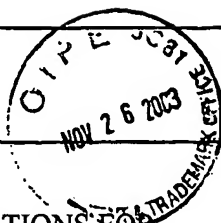
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Filing Date:  
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	Applicant: Jae-Hyun Ryou et al.		
	Filing Date: June 27, 2003	Group Art: <del>unknown</del> 2828	



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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	Applicant: Jae-Hyun Ryou et al.	
	Filing Date: June 27, 2003	Group Art: <del>unknown</del> 2828

TN	U.S. Patent Application Serial No. 09/751,422, filed December 29, 2000, entitled "Resonant Reflector for Use with Optoelectronic Devices".
	U.S. Patent Application Serial No. 09/751,423, filed December 29, 2000, entitled "Spatially Modulated Reflector for an Optoelectronic Device".

EXAMINER: <i>Tuan Nguyen</i>	DATE CONSIDERED: <i>2/16/05</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.